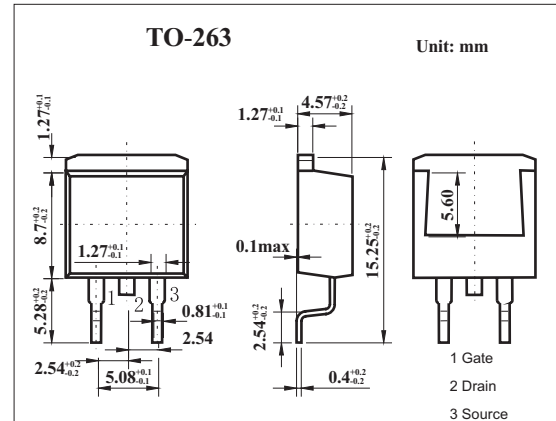
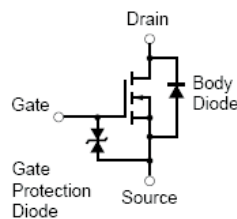


MOS Field Effect Transistor

2SK3111

■ Features

- Gate voltage rating ± 30 V
- Low on-state resistance
 $R_{DS(on)} = 180\text{m}\Omega$ MAX. ($V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$)
- Low input capacitance
 $C_{iss} = 1000\text{ pF}$ TYP. ($V_{DS} = 10\text{ V}$, $V_{GS} = 0\text{ V}$)
- Avalanche capability rated
- Built-in gate protection diode
- Surface mount device available



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DS}	200	V
Gate to source voltage	V_{GS}	± 30	V
Drain current	I_D	± 20	A
	I_{DP}^*	± 60	A
Power dissipation	P_D	62	W
		1.5	
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10\text{ }\mu\text{s}$, Duty Cycle $\leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS}=200\text{ V}, V_{GS}=0$			100	$\mu\text{ A}$
Gate leakage current	I_{GSS}	$V_{GS}=\pm 30\text{ V}, V_{DS}=0$			± 10	$\mu\text{ A}$
Gate to source cut off voltage	$V_{GS(off)}$	$V_{DS}=10\text{ V}, I_D=1\text{ mA}$	2.5		4.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=10\text{ V}, I_D=10\text{ A}$	3.0			S
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=10\text{ A}$		120	180	$\text{m}\Omega$
Input capacitance	C_{iss}	$V_{DS}=10\text{ V}, V_{GS}=0, f=1\text{ MHz}$		1000		pF
Output capacitance	C_{oss}			300		pF
Reverse transfer capacitance	C_{rss}			150		pF
Turn-on delay time	t_{on}	$I_D=10\text{ A}, V_{GS(on)}=10\text{ V}, V_{DD}=100\text{ V}, R_G=10\text{ }\Omega$		25		ns
Rise time	t_r			90		ns
Turn-off delay time	t_{off}			80		ns
Fall time	t_f			40		ns